5 é / Descriptions

TO-252 .> / / x 9 O) N ?ú 3 MOS « | • ’ož

SiC N-CHANNEL MOSFET in a TO-252 Plastic Package.

¤ ª / Features

V_{DS}=800V z I_D=6.9A

$R_{DS(on)}$@15V ”1300m (Type.1000m)

Ð ÷ / Applications

• ¼ ›o• ä 9 *) *) ô E ˜o• P - ˜o• Ñ Ü o• Ï ä • ož

Switch Mode Power Supplies,High Voltage DC/DC Converters,Battery Chargers,Motor Drives,Pulsed Power Applications.

Ã W] Ô · / Equivalent Circuit

• Û - æ / Pinning

PIN1 y G PIN 2 y D PIN 3 y S PIN 4 y D

, M V / Marking

• - ~ ª ¢ož

See Marking Instructions.

Ô ? d • Ž ¢ / Electrical Characteristic Curve

Ô ? d • Ž ¢ / Electrical Characteristic Curve

BRSC80R1K0ZDP

Ø ¤ =) ¢ / Package Dimensions

, M y ƒ / Marking Instructions

BR
65R1K0Z
SC ****

ª ¢ y

BR y ¸ [W A

8 1 @ y º Z W A

9) y K J´

y ÿ D Z W A k š ÿ D Z J

Note:

BR:	Company Code
65R1K0Z:	Product Type Code
SC:	SiC
****:	Lot No. Code, code change with Lot No.

š WD t … • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6

ª ¢ y

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q › “ † 245 r 5 - k ž • 4 Ò 5 r 0.5sec;

3o•D N ò i Ò 0 , † r

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r 5 - , Duration:5 r 0.5sec.